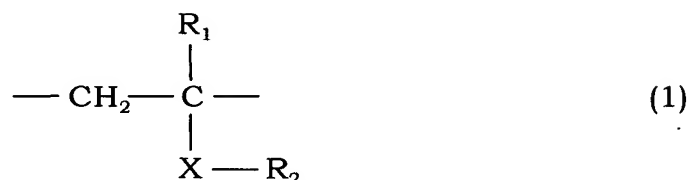


Abstract of the Disclosure

A via-filling material comprising a polymer containing a repeat unit represented by the following formula (1):



wherein R_1 is a member selected from the group consisting of hydrogen atom, fluorine atom, chlorine atom, bromine atom and methyl group; R_2 is a member selected from the group consisting of hydrogen atom, C_{1-3} alkyl group and C_{1-4} alkyl group in which the hydrogen atom is substituted by at least one kind of atoms of fluorine, chlorine and bromine atom; and X is ---C(=O)O--- or $\text{---S(=O)}_2\text{O---}$ is used as the via-filling material. This via-filling material does not generate deposition around the opening part of a via hole and provides a semiconductor integrated circuit with high reliability even when a trench wider than the via hole is formed by etching the via hole filled with the via-filling material with plasma.